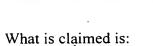
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1.	A process for forming an article, comprising the steps of:
provid	ling a substrate, and

forming on the substrate a film of $(BiEu)_3(Fe_{5-y}(Ga_xAl_{1-x})_y) O_{12}$, where x is 0 to 1 and y is 0.8 to 1.2,

wherein the substrate is a single crystal material consisting essentially of a solid solution of two or more garnet materials, the substrate having a lattice parameter within 0.004 Angstrom of the lattice parameter of the (BiEu)₃(Fe_{5-y}(Ga_xAl_{1-x})_y) O₁₂.

- 2. The process of claim 1, wherein x is 1, and the substrate lattice parameter is 12.53 to 12.555 Angstroms.
- 3. The process of claim 1, wherein the substrate is of substantially uniform composition.
- 4. The process of claim 1, wherein the substrate consists essentially of a solid solution of gadolinium scandium gallium garnet and gadolinium scandium aluminum garnet, or a solid solution of gadolinium scandium gallium garnet and terbium scandium gallium garnet.
- 5. The process of claim 1, wherein y is selected such that the film exhibits a saturation magnetization, in absolute value, less than 100G at least at room temperature.
- 6. The process of claim 5, wherein the film exhibits a substantially rectangular magnetization loop, a saturation magnetization, in absolute value, less than 100G, a switching field, in absolute value, higher than the saturation magnetization, in a magnetic field applied parallel to the normal to the major surface of the film, over an operating temperature range of -40°C to +85°C.

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- 7. The process of claim 6, wherein the film exhibits a switching field, in absolute value, of at least 200 Oe over the operating temperature range, and a switching field, in absolute value, of at least 500 Oe at least at room temperature.
- 1 8. The process of claim 7, wherein the film exhibits a switching field, in 2 absolute value, of 500 Oe or higher over the operating temperature range.
- 9. The process of claim 1, further comprising the steps of:
 processing the film to form chips, and
 incorporating at least one chip into a device.
 - 10. The process of claim 1, wherein the lattice parameter is within 0.002 Angstrom of the lattice parameter of the $(BiEu)_3(Fe_{5-y}(Ga_xAl_{1-x})_y) O_{12}$.
 - A process for forming an article, comprising the steps of: providing a substrate, and

forming on the substrate a film of $(BiEu)_3(Fe_{5-y}(Ga_xAl_{1-x})_y) O_{12}$, where x is 0 to 1 and y is 0.8 to 1.2,

wherein the substrate is a single crystal material consisting essentially of a solid solution of gadolinium scandium gallium garnet and gadolinium scandium aluminum garnet, or a solid solution of gadolinium scandium gallium garnet and terbium scandium gallium garnet.

- 12. The process of claim 11, where x is 1.
- 1 13. The process of claim 12, wherein the substrate lattice parameter if 12.53 to 12.555 Angstroms.
- 1 14. The process of claim 13, wherein the substrate is of substantially uniform 2 composition.

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- 15. The process of claim 11, wherein y is selected such that the film exhibits a saturation magnetization, in absolute value, less than 100G at least at room temperature.
 - 16. The process of claim 15, wherein the film exhibits a substantially rectangular magnetization loop, a saturation magnetization, in absolute value, less than 100G, a switching field, in absolute value, higher than the saturation magnetization, in a magnetic field applied parallel to the normal to the major surface of the film, over an operating temperature range of -40°C to +85°C.
 - 17. The process of claim 13, wherein the film exhibits a switching field, in absolute value, of at least 200 Oe over the operating temperature range, and a switching field, in absolute value, of at least 500 Oe at least at room temperature.
 - 18. The process of claim 17, wherein the film exhibits a switching field, in absolute value, of 500 Oe or higher over the operating temperature range.
 - 19. The process of claim 11, further comprising the steps of: processing the film to form chips, and incorporating at least one chip into a device.
 - 20. An article comprising the film according to claim 1.
- 1 21. An article comprising the film according to claim 4.